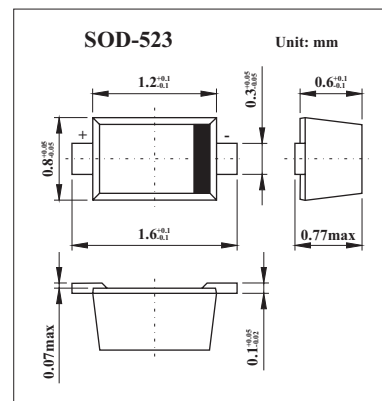


RF PIN Diode

BAR65V-02V

■ Features

- Space saving SOD523 package with low series inductance
- Very small reverse capacitance
- Small reverse capacitance

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	30	V
Forward current	I_F	100	mA
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Junction soldering point	R_{thJS}	100	K/W

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse voltage	V_R	$I_R = 10\ \mu\text{A}$	30			V
Reverse current	I_R	$V_R = 20\ \text{V}$			20	nA
Forward voltage	V_F	$I_F = 100\ \text{mA}$			1.1	V
Diode capacitance	C_D	$f = 1\ \text{MHz}, V_R = 0$		0.65		pF
		$f = 1\ \text{MHz}, V_R = 1\ \text{V}$		0.55	0.9	
		$f = 1\ \text{MHz}, V_R = 3\ \text{V}$		0.50	0.8	
Forward resistance	r_f	$f = 100\ \text{MHz}, I_F = 1\ \text{mA}$		1		Ω
		$f = 100\ \text{MHz}, I_F = 5\ \text{mA}$		0.6	0.95	
		$f = 100\ \text{MHz}, I_F = 10\ \text{mA}$		0.52	0.9	
Charge carrier life time	t_{rr}	$I_F = 10\ \text{mA}, I_R = 6\ \text{mA}, i_R = 3\ \text{mA}$		150		ns

■ Marking

Marking	E
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